

09/943199

Cope
JAN 18 2006



Docket No.: M4065.0704/P704
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Kristy A. Campbell et al.

Patent No.: 6,955,940 B2

Issued: October 18, 2005

For: METHOD OF FORMING CHALCOGENIDE
COMPRISING DEVICES

Certificate
JAN 18 2006
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322 & 1.323

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the Foreign Patent Documents portion of the References Cited Section, Applicants made the following error to be corrected:

"WO 97/488032" should read --WO 97/48032--.

In field (74) *Attorney, Agent, or Firm*, the PTO misspelled the name of the firm:

"Dickstein Shaprio Morin & Oshinsky LLP" should read --Dickstein Shapiro Morin & Oshinsky LLP--.

01/12/2006 SZEWDIE1 00000047 6955940

01 FC:1811

100.00 DP

DSMDB.2026449.1

JAN 18 2006

In the Abstract, line 10, Applicants made the following error to be corrected:

"to and HNO₃" should read --to an HNO₃--.

In the Other Publications portion of the References Cited section, the PTO made the following errors:

"Hirose, et al , "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As₂S₃ films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pps 2767-2772."

Should read

--Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As₂S₃ films", Journal of Applied Physics, Vol. 47, No. 6, Jun. 1976, pps 2767-2772.--;

"Kluge, et al , "Silver photodiffusion in amorphous Ge_xSe_{100-x}", Journal of Non-Crystalline Solids 124 (1990) pps 186-193."

Should read

--Kluge, et al., "Silver photodiffusion in amorphous Ge_xSe_{100-x}", Journal of Non-Crystalline Solids 124 (1990) pps 186-193.--;

"Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances in Physics No. 6, 475-588 (Taylor & Francis 1995)."

Should read

--Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances in Physics No. 6, 475-588 (Taylor & Francis 1995).--;

"Drusdau, T.P.; Panckow, A.N.; Klabunda, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832."

Should read

--Drusdau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system--Films of unique electronic properties, *J. Non-Cryst. Solids* 198-200 (1996) 829-832.--;

"Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, *J. Non-Cryst. Solids* 298 (2002) 260-269."

Should read

--Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, *J. Non-Cryst. Solids* 298 (2002) 260-269.--;

"Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, *J. Am. Ceram. Soc.* 85 (2002) 1545-52."

Should read

--Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, *J. Am. Ceram. Soc.* 85 (2002) 1545-52.--;

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe₂ Crystals, *Science* 258 (1992) 271-274."

Should read

--Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-temperature, electric field induced creation of stable devices in CuInSe₂ crystals, *Science* 258 (1992) 271-274.--;

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, *Thin Solid Films* 240 (1994) 143-146."

Should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, *Thin Solid Films* 240 (1994) 143-146.--; and

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Legarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985."

Should read

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors. Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985.--

Also in the Other Publications portion of the References Cited section, Applicants made the following error to be corrected:

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080."

Should read

--Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.--

In the Specification, Applicants made the following errors to be corrected:

Column 3, line 45, "example only, example" should read --example only--; and

Column 6, line 52, "comprises and oxide" should read --comprises an oxide--.

In the Claims, the PTO made the following error to be corrected:

Claim 13, column 9, line 17, "atomosphere" should read --atmosphere--.

The errors were made primarily by the PTO but were also found in the application as filed by applicant. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0704/P704. A duplicate copy of this paper is enclosed.

Dated: January 10, 2006

Respectfully submitted,

By 
Thomas J. D'Amico

Registration No.: 28,371

Peter McGee

Registration No.: 35,947

DICKSTEIN SHAPIRO MORIN &

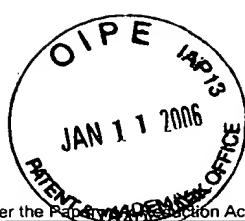
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicants



PTO/SB/17 (12-04v2)

Approved for use through 7/31/2006. OMB 0651-0032

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number.

Effective on 12/08/2004.

Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).

FEE TRANSMITTAL For FY 2005

 Applicant claims small entity status. See 37 CFR 1.27

TOTAL AMOUNT OF PAYMENT (\$ 100.00)

Complete if Known

Application Number	Patent#: 6,955,940 B2
Filing Date	Issued: October 18, 2005
First Named Inventor	Kristy A. Campbell
Examiner Name	D. Vu
Art Unit	2818
Attorney Docket No.	M4065.0704/P704

METHOD OF PAYMENT (check all that apply)

Check Credit Card Money Order None Other (please identify): _____
 Deposit Account Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP

For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)

<input checked="" type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input type="checkbox"/> Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

FEE CALCULATION**1. BASIC FILING, SEARCH, AND EXAMINATION FEES**

<u>Application Type</u>	<u>FILING FEES</u>		<u>SEARCH FEES</u>		<u>EXAMINATION FEES</u>		
	<u>Fee (\$)</u>	<u>Small Entity</u>	<u>Fee (\$)</u>	<u>Small Entity</u>	<u>Fee (\$)</u>	<u>Small Entity</u>	<u>Fees Paid (\$)</u>
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	

2. EXCESS CLAIM FEESFee Description

Each claim over 20 (including Reissues)	<u>Fee (\$)</u>	<u>Small Entity</u>
	50	25
Each independent claim over 3 (including Reissues)	200	100

Multiple dependent claims

<u>Total Claims</u>	<u>Extra Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>	<u>Multiple Dependent Claims</u>
- =	x	=		<u>Fee (\$)</u> <u>Fee Paid (\$)</u>
<u>Indep. Claims</u>	<u>Extra Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>	- - - - -

3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

<u>Total Sheets</u>	<u>Extra Sheets</u>	<u>Number of each additional 50 or fraction thereof</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>
_____ - 100 =	/50	(round up to a whole number) x	=	

4. OTHER FEE(S)

Non-English Specification, \$130 fee (no small entity discount)

Other (e.g., late filing surcharge): 1811 Certificate of correction

100.00

SUBMITTED BY

Signature		Registration No. (Attorney/Agent)	28,371	Telephone	(202) 828-2232
Name (Print/Type)	Thomas J. D'Amico			Date	January 10, 2006

JAN 18 2006

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

Page 1 of 3

PATENT NO. : 6,955,940 *B2*
 APPLICATION NO. : 09/943,199
 ISSUE DATE : October 18, 2005
 INVENTOR(S) : Kristy A. Campbell et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Foreign Patent Documents portion of the References Cited Section, the following error is corrected:

"WO 97/488032" should read --WO 97/48032--.

In field (74) *Attorney, Agent, or Firm*, the name of the firm is corrected as follows:

"Dickstein Shapiro Morin & Oshinsky LLP" should read --Dickstein Shapiro Morin & Oshinsky LLP--.

In the Abstract, line 10, the following error is corrected:

"to and HNO₃" should read --to an HNO₃--.

In the Other Publications portion of the References Cited section, the following errors are corrected:

"Hirose, et al , "Polanty-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As₂S₃ films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pps 2767-2772."

Should read

--Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As₂S₃ films", Journal of Applied Physics, Vol. 47, No. 6, Jun. 1976, pps 2767-

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
 DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 1
 2101 L Street NW
 Washington, DC 20037-1526

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-274."

Should read

--Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-temperature, electric field induced creation of stable devices in CuInSe₂ crystals, Science 258 (1992) 271-274.--;

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

Should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.--;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Legarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985."

Should read

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors. Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985.--. and

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080."

Should read

--Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.--.

In the Specification, the following errors are corrected:

Column 3, line 45, "example only, example" should read --example only,--; and

Column 6, line 52, "comprises and oxide" should read --comprises an oxide--.

In the Claims, the following error is corrected:

Claim 13, column 9, line 17, "atomosphere" should read --atmosphere--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico

DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 3

2101 L Street NW

Washington, DC 20037-1526

JAN 18 2006

2772.--;

"Kluge, et al , "Silver photodiffusion in amorphous Ge_xSe_{100-x}", Journal of Non-Crystalline Solids 124 (1990) pps 186-193."

Should read

--Kluge, et al., "Silver photodiffusion in amorphous Ge_xSe_{100-x}", Journal of Non-Crystalline Solids 124 (1990) pps 186-193.--;

"Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances in Physics No. 6, 475-588 (Taylor & Francis 1995)."

Should read

--Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances in Physics No. 6, 475-588 (Taylor & Francis 1995).--;

"Drusdau, T.P.; Panckow, A.N.; Klabunda, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832."

Should read

--Drusdau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.--;

"Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269."

Should read

--Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.--;

"Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52."

Should read

--Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.--;

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2
2101 L Street NW
Washington, DC 20037-1526

JAN 18 2006